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Attorney Docket No. 5308-156

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.

U.S. Patent No.: 6,956,238 ^{B2}

Application Serial No.: 09/911,995

Issued: October 18, 2005

Filed: July 24, 2001

For: *Silicon Carbide Power Metal-Oxide Semiconductor Field Effect Transistors Having A Shorting Channel and Methods of Fabricating Silicon Carbide Metal-Oxide Semiconductor Field Effect Transistors Having a Shorting Channel*

Date: March 16, 2006

Commissioner for Patents
Attn: Certificate of Correction Branch
P.O. Box 1450
Alexandria, VA 22313-1450

**REQUEST FOR ENTRY OF CERTIFICATE OF CORRECTION UNDER
35 U.S.C §254 AND 37 C.F.R. §1.322**

Sir:

The Assignee of record for the above-referenced patent hereby requests, pursuant to 35 U.S.C §254 and 37 C.F.R. §1.322, that a Certificate of Correction be issued. This request is made in order to correct the mistakes incurred through the fault of the U.S. Patent and Trademark Office. No fee is believed due. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

The mistakes appearing in the patent are set forth with corrections on the Certificate of Correction enclosed herewith, with an additional copy thereof and a return post card.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

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Monica L. Croom

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Section 60 should include -- Application No. 09/834,283, filed on Apr. 12, 2001, now Pat. No. 6,610,366. --

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